

Sheet 1 of 2

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## U.S. PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	5,668,035	09/16/1997	Fang, C.H., et al.	438	239	06/10/96
	5,985,725	11/16/1999	Chou, J.	438	294	12/23/97
	6,087,225	07/11/2000	Bronner, G.B., et al.	438	275	02/05/98
	6,097,056	08/01/2000	Hsu, L.L., et al.	257	315	04/28/98
	6,222,788	04/01/2001	Forbes, et al.	365	230.06	

## FOREIGN PATENT DOCUMENTS

**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes   No
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## OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages, Etc.)

**Examiner Initial	Chen, Y., et al., "Performance and Reliability Assessment of Dual-Gate CMOS Devices with Gate Oxide Grown Nitrogen Implanted Si Substrates", <u>International Electron Device Meeting</u> , pg. 1-4, (1997)
	Cho, I.H., et al., "Highly Reliable Dual Gate Oxide Fabrication by Reducing Wet Etching Time and Re-Oxidation for Sub-Quarter Micron CMOS Devices", <u>Extended Abstracts of the 1999 International Conference on Solid State Devices and Materials</u> , pgs. 174-175, (1999)
	Crowder, S., et al., "Trade-offs in the Integration of High Performance Devices with Trench Capacitor DRAM", <u>Dig. Int. Electron Devices Meeting, Washington, D.C.</u> , pp. 45-48, (Dec. 1997)
	Fujiwara, M., et al., "New Optimization Guidelines for Sub-0.1 micrometer CMOS Technologies with 2 micrometer NO Gate Oxynitrides", <u>1999 Symposium on VLSI Technology Digest of Technical Papers</u> , pp. 121-122, (1999)
	Guo, X., et al., "High Quality Ultra-thin TiO <sub>2</sub> /Si <sub>3</sub> N <sub>4</sub> Gate Dielectric for Giga Scale MOS Technology", <u>Technical Digest of 1998 IEDM</u> , pp. 377-380, (1998)
	Han, L.K., et al., "Electrical Characteristics and Reliability of sub-3 nm Gate Oxides Grown on Nitrides Implanted Silicon Substrates", <u>Int. Electron Devices Meeting, Washington, D.C.</u> , pp. 1-4, (1997)

Examiner	Date Considered

\*Substitute Disclosure Statement Form (PTO-1449)

\*\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.